

Docket No.: GR 98 P 1379 D

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P. 13, 14  
8/2/01



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Lars-Peter Heineck et al.  
Div. of Applic. No. : 09/272,968, filed March 19, 1999  
Div. filed : June 20, 2001  
Title : MOS Transistor in a Single-Transistor Memory Cell Having a Locally Thickened Gate Oxide  
Examiner : Hoai Pham Group Art Unit: 2814

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,  
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are cited herewith:

U.S. Patent No. 5,306,655 (Kurimoto), dated April 26, 1994.

U.S. Patent No. 5,360,758 (Bronner et al.), dated November 1, 1994;

Above-mentioned references cited in an Information Disclosure Statement dated March 19, 1999, in parent application No. 09/272,968.

U.S. Patent No. 5,612,249 (Sun et al.), dated March 18, 1997;

U.S. Patent No. 5,798,550 (Kuroyanagi et al.), dated August 25, 1998;

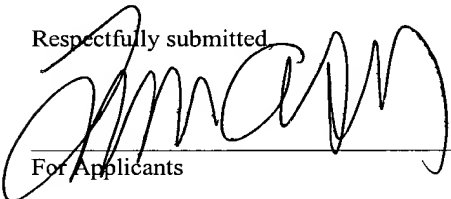
U.S. Patent No. 6,015,736 (Luning et al.), dated January, 2000.

Above-mentioned references cited in an Office Action dated March 2, 2000, in parent application No. 09/272,968.

U.S. Patent No. 5,637,514 (Jeng et al.), dated June, 1997.

Above-mentioned reference cited in an Office Action dated October 5, 2000, in parent application No. 09/272,968.

Respectfully submitted

A large, stylized handwritten signature in black ink, appearing to read 'L. Greenberg', written over a horizontal line.

For Applicants

**LAURENCE A. GREENBERG**  
**REG. NO. 29,308**

Date: June 20, 2001

Lerner and Greenberg, P.A.  
Post Office Box 2480  
Hollywood, FL 33022-2480  
Tel: (954) 925-1100  
Fax: (954) 925-1101  
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